



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

19/10 Chusa
2-20-02

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/471,460

Filed: December 22, 1999

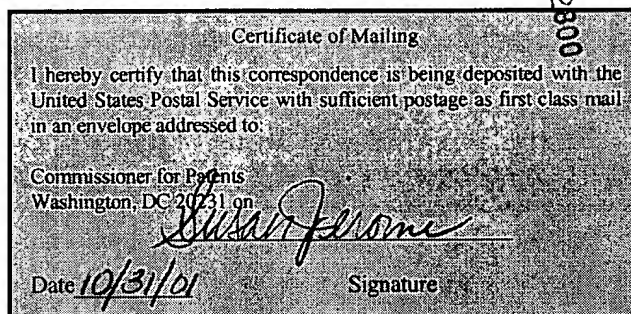
Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§
§ Group Art Unit: 2825
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§ Application Examiner: Calvin Lee
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§ Atty. Docket: 94-0280.03
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AMENDMENT AND RESPONSE TO THE
OFFICE ACTION DATED JULY 31, 2001

Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

Applicants submit this Amendment and Response to the Office Action dated July 31, 2001. Please amend the above-captioned application as follows.

IN THE CLAIMS

- ✓ Please cancel claim 44 without prejudice.
- ✓ Please amend claim 45 to the following form.

45. (Twice amended) A method of providing a polymer between metal features on a wafer, comprising:

performing a deposition on said wafer in a site; and

etching in the same general site used to perform said deposition, wherein said step

of etching further comprises etching generally simultaneously with

performing said deposition.